



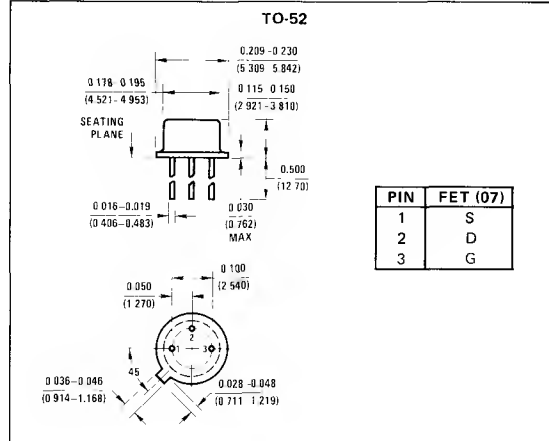
## 2N5432-34 N-Channel JFETs

### General Description

The 2N5432 thru 2N5434 series of N-channel JFETs is designed for analog switch applications requiring very low ON resistance.

### Absolute Maximum Ratings (25°C)

Reverse Gate-Drain or Gate-Source Voltage	-25V
Gate Current	100 mA
Drain Current	400 mA
Total Device Dissipation at 25°C	
Free-Air Temperature, (Note 1)	300 mW
Storage Temperature Range	-65°C to +200°C
Lead Temperature (1/16" from case for 10 seconds)	300°C

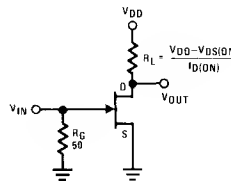


### Electrical Characteristics (25°C unless otherwise noted)

PARAMETER	CONDITIONS	2N5432		2N5433		2N5434		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
IGSS Gate Reverse Current	VGS = -15V, VDS = 0 150°C		-200		-200		-200	pA
								nA
BVGSS Gate-Source Breakdown Voltage	IG = -1 μA, VDS = 0	-25		-25		-25		V
ID(off) Drain Cutoff Current	VDS = 5V, VGS = -10V 150°C		200		200		200	pA
			200		200		200	nA
VGS(off) Gate-Source Cutoff Voltage	VDS = 5V, ID = 3 nA	-4	-10	-3	-9	-1	-4	V
IDSS Saturation Drain Current	VDS = 15V, VGS = 0, (Note 2)	150		100		30		mA
rDS(on) Static Drain-Source ON Resistance	VGS = 0, ID = 10 mA	2	5	7		10		Ω
VDS(on) Drain-Source ON Voltage			50	70	100			mV
rds(on) Drain-Source ON Resistance	VGS = 0, ID = 0 f = 1 kHz		5	7		10		Ω
Ciss Common-Source Input Capacitance	VDS = 0, VGS = -10V f = 1 MHz		30	30		30		pF
Crss Common-Source Reverse Transfer Capacitance			15	15		15		
td Turn ON Delay Time	VDD = 1.5V, VGS(on) = 0, VGS(off) = -12V, ID(on) = 10 mA		4	4		4		ns
tr Rise Time			1	1		1		
toff Turn OFF Delay Time			6	6		6		
tf Fall Time			30	30		30		

Note 1: Derate linearly at the rate of 2.3 mW/°C.

Note 2: Pulse test required pulse width 300 μs, duty cycle ≤ 3%.



#### Input Pulse

Rise time = 0.25 ns  
Fall time = 0.75 ns  
Pulse width = 200 ns  
Pulse rate = 550 pps

#### Sampling Scope

Rise time = 0.4 ns  
Input resistance = 10M  
Input Capacitance = 1.5 pF